

CLAIM AMENDMENTS

1-29. (Canceled)

30. (New) A method of supplying a solution for electrochemical deposition and removal to a surface of a substrate from an assembly having a housing with an internal volume divided by a filter into a first chamber containing an electrode and a second chamber located between the first chamber and the surface, the process comprising:

supplying the solution into the first chamber through a first flow channel;
supplying the solution into the second chamber through a second flow channel; and
flowing the solution from the second chamber towards the surface.

31. (New) The method of Claim 30, wherein the solution is supplied into the second chamber at a flow rate higher than the solution supplied into the first chamber.

32. (New) The method of Claim 31, wherein the solution supplied through the second flow channel is more than 60 percent of the solution that is supplied through the first and second flow channels.

33. (New) The method of Claim 30, wherein the solution is an electrolyte out of which a conductive film is deposited onto the surface of the substrate.

34. (New) The method of Claim 30, further comprising flowing the solution out of the first chamber in a controlled manner.

35. (New) A method of supplying a solution for electrochemical deposition and removal to a surface of a substrate from a processing assembly having a housing with an internal volume divided by a filter into a first chamber containing an electrode and a second chamber located between the first chamber and the surface of the substrate, the method comprising:

supplying the solution into the first chamber through a first flow channel while flowing the solution out of the first chamber in a controlled manner;

supplying the solution into the second chamber through a second flow channel; and

flowing the solution from the second chamber towards the surface of the substrate.

36. (New) The method of Claim 35, wherein the solution is supplied into the second chamber at a flow rate higher than the solution supplied into the first chamber.

37. (New) The method of Claim 36, wherein the solution supplied through the second flow channel is more than 60 percent of the solution that is supplied through the first and second flow channels.

38. (New) The method of Claim 35, wherein the substrate includes a semiconductor wafer.

39. (New) The method of Claim 35, wherein the solution is an electrolyte out of which a conductive film is deposited onto the surface of the substrate.

40. (New) The method of Claim 35, wherein the solution is a polishing solution used for removing material from the surface of the substrate.

41. (New) A method of supplying a solution for electrochemical deposition and removal to a surface of a substrate received in a process assembly having a housing with an internal volume divided by a primary filter into a first chamber and a second chamber, wherein an electrode is placed in the first chamber and the second chamber is separated from the surface of the wafer by a upper filter, comprising:

supplying the solution into the first chamber through a first flow channel while flowing the solution out the first chamber in a controlled manner;

supplying the solution into the second chamber through a second flow channel; and

flowing the solution through the upper filter to the surface of the wafer.

42. (New) The method of Claim 41, wherein the solution is supplied into the second chamber at a flow rate higher than the solution supplied into the first chamber.

43. (New) The method of Claim 42, wherein the solution supplied through the second flow channel is more than 60 percent of the solution that is supplied through the first and second flow channels.

44. (New) The method of Claim 41, further comprising flowing the solution through a polishing pad after flowing the solution through the upper filter.

45. (New) The method of Claim 41, further comprising filtering the solution before supplying through the first and second flow channels.